TOSHIBA TA4012F

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA4012F

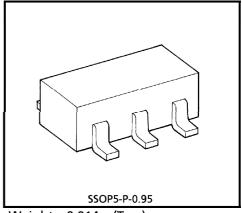
UHF WIDE BAND AMPLIFIER APPLICATIONS

FEATURES

Low Current $: I_{CC} = 6.5 \text{mA}$

Wide Band : f = 2.0GHz (3dB down)

Operating Supply Voltage: V_{CC} = 1.5~3V



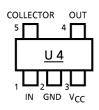
Weight: 0.014g (Typ.)

MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	VCC	4	V
Total Power Dissipation	P _D (Note 1)	300	mW
Operating Temperature	T _{opr}	- 40∼85	°C
Storage Temperature	T _{stg}	- 55∼150	°C

(Note 1) When mounted on the glass epoxy of 2.5cm² x 1.6t

PIN ASSIGNMENT



CAUTION

This device electrostatic sensitivity. Please handle with caution.

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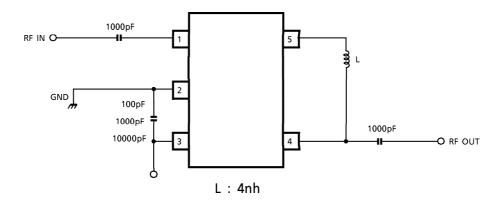
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ELECTRICAL CHARACTERISTICS (Ta = 25°C, Zg = ZI = 50 Ω)

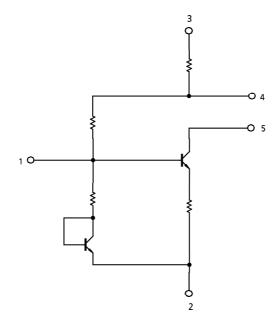
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Circuit Current	lcc	V _{CC} = 2V, Non carrier	4.5	6.5	8.5	mA
Band Width	BW	V _{CC} = 2V (Note 2)	1.8	2.0	_	GHz
Insertion Gain	S21 ²	V _{CC} = 2V, f = 1.5GHz	10	12	_	dB
Noise Figure	NF	V _{CC} = 2V, f = 1.5GHz	_	6	7.5	dB
Isolation	S12 ²	V _{CC} = 2V, f = 1.5GHz	_	- 22	_	dB
Input Return Loss	S11 ²	V _{CC} = 2V, f = 1.5GHz	_	- 6.5	_	dB
Output Return Loss	S22 ²	V _{CC} = 2V, f = 1.5GHz	_	- 7.5	_	dB
Output Power at 1dB Gain Compression	Po1dB	V _{CC} = 2V, f = 1.5GHz	_	0	_	dBmW

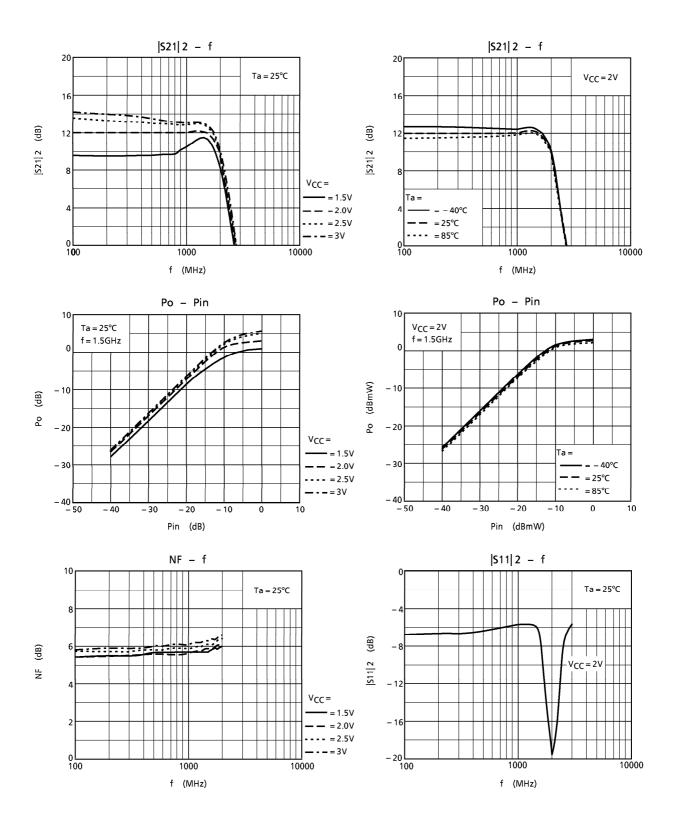
(Note 2) BW is the frequency of 3dB down from $|S21|^2$ at 1.5GHz.

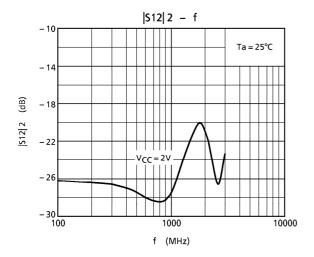
RF TEST CIRCUIT (TOP VIEW)

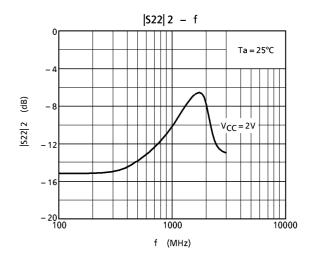


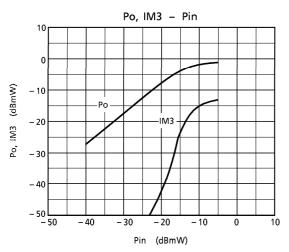
EQUIVALENT CIRCUIT

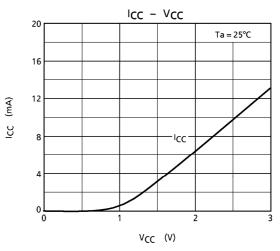






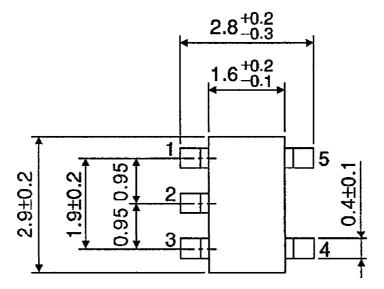


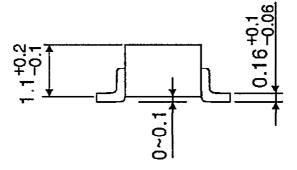




OUTLINE DRAWING SSOP5-P-0.95

Unit: mm





Weight: 0.014g (Typ.)